

# **RGW80TS65**

### 650V 40A Field Stop Trench IGBT

V <sub>CES</sub>	650V
I <sub>C (100°C)</sub>	40A
V <sub>CE(sat) (Typ.)</sub>	1.5V
$P_D$	214W

## ● Features

- 1) Low Collector Emitter Saturation Voltage
- 2) High Speed Switching
- 3) Low Switching Loss & Soft Switching
- 4) Pb free Lead Plating; RoHS Compliant

#### Applications

**PFC** 

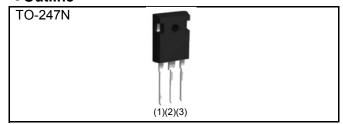
**UPS** 

Welding

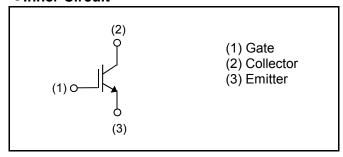
Solar Inverter

ΙH

#### Outline



#### ●Inner Circuit



Packaging Specifications

	<del></del>	
	Packaging	Tube
	Reel Size (mm)	-
Typo	Tape Width (mm)	-
Type Basic	Basic Ordering Unit (pcs)	450
	Packing Code	C11
	Marking	RGW80TS65

#### ● Absolute Maximum Ratings (at T<sub>C</sub> = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit
Collector - Emitter Voltage		V <sub>CES</sub>	650	V
Gate - Emitter Voltage		V <sub>GES</sub>	±30	V
Collector Current	T <sub>C</sub> = 25°C	I <sub>C</sub>	78	А
Collector Current	T <sub>C</sub> = 100°C	I <sub>C</sub>	40	А
Pulsed Collector Current		I <sub>CP</sub> *1	160	А
Power Discinction	T <sub>C</sub> = 25°C	P <sub>D</sub>	214	W
Power Dissipation	T <sub>C</sub> = 100°C	P <sub>D</sub>	107	W
Operating Junction Temperature		Tj	-40 to +175	°C
Storage Temperature		T <sub>stg</sub>	-55 to +175	°C

<sup>\*1</sup> Pulse width limited by T<sub>imax</sub>.

#### ●Thermal Resistance

Parameter	Symbol	Values			Unit
- Faranietei	Symbol	Min.	Тур.	Max.	Offic
Thermal Resistance IGBT Junction - Case	$R_{\theta(j-c)}$	-	-	0.70	°C/W

## ●IGBT Electrical Characteristics (at T<sub>j</sub> = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
r ai ai nietei	Symbol Conditions –		Min.	Тур.	Max.	Offic
Collector - Emitter Breakdown Voltage	BV <sub>CES</sub>	$I_{C} = 10 \mu A, V_{GE} = 0 V$	650	-	-	V
Collector Cut - off Current	I <sub>CES</sub>	V <sub>CE</sub> = 650V, V <sub>GE</sub> = 0V	1	1	10	μΑ
Gate - Emitter Leakage Current	I <sub>GES</sub>	$V_{GE} = \pm 30V, V_{CE} = 0V$	-	-	±200	nA
Gate - Emitter Threshold Voltage	$V_{\text{GE(th)}}$	$V_{CE} = 5V, I_{C} = 26.0 \text{mA}$	5.0	6.0	7.0	٧
Collector - Emitter Saturation Voltage	V <sub>CE(sat)</sub>	$I_C = 40A$ , $V_{GE} = 15V$ $T_j = 25$ °C $T_j = 175$ °C	-	1.5 1.85	1.9	٧

## ●IGBT Electrical Characteristics (at T<sub>j</sub> = 25°C unless otherwise specified)

Daramatar	Cymphal	Conditions		Values		
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input Capacitance	C <sub>ies</sub>	V <sub>CE</sub> = 30V	-	3320	-	
Output Capacitance	C <sub>oes</sub>	V <sub>GE</sub> = 0V	-	83	-	pF
Reverse Transfer Capacitance	C <sub>res</sub>	f = 1MHz	-	60	-	
Total Gate Charge	$Q_g$	V <sub>CE</sub> = 400V	-	110	-	
Gate - Emitter Charge	$Q_{ge}$	I <sub>C</sub> = 40A	-	23	-	nC
Gate - Collector Charge	$Q_{gc}$	V <sub>GE</sub> = 15V	-	41	-	
Turn - on Delay Time	t <sub>d(on)</sub>	I <sub>C</sub> = 40A, V <sub>CC</sub> = 400V	-	44	-	
Rise Time	t <sub>r</sub>	$V_{GE} = 15V, R_{G} = 10\Omega$	-	17	-	
Turn - off Delay Time	t <sub>d(off)</sub>	T <sub>j</sub> = 25°C	-	143	-	ns
Fall Time	t <sub>f</sub>	Inductive Load	-	34	-	
Turn - on Switching Loss	E <sub>on</sub>	*E <sub>on</sub> includes diode	-	0.76	-	
Turn - off Switching Loss	E <sub>off</sub>	reverse recovery	-	0.72	-	mJ
Turn - on Delay Time	t <sub>d(on)</sub>	I <sub>C</sub> = 40A, V <sub>CC</sub> = 400V	-	41	-	
Rise Time	t <sub>r</sub>	$V_{GE} = 15V, R_G = 10\Omega$	-	18	-	no
Turn - off Delay Time	$t_{d(off)}$	T <sub>j</sub> = 175°C	-	158	-	ns
Fall Time	t <sub>f</sub>	Inductive Load	-	74	-	
Turn - on Switching Loss	E <sub>on</sub>	*E <sub>on</sub> includes diode	-	0.76	-	m l
Turn - off Switching Loss	E <sub>off</sub>	reverse recovery	-	0.91	-	mJ
		I <sub>C</sub> = 160A, V <sub>CC</sub> = 520V				
Reverse Bias Safe Operating Area	RBSOA	V <sub>P</sub> = 650V, V <sub>GE</sub> = 15V	FU	LL SQUA	RE	-
1		$R_G = 100\Omega, T_j = 175^{\circ}C$				

#### • Electrical Characteristic Curves

Fig.1 Power Dissipation vs. Case Temperature

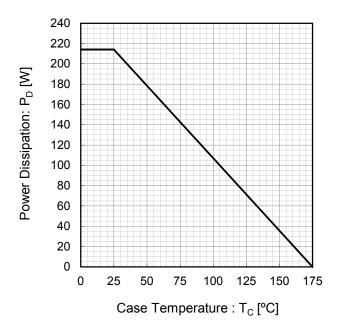


Fig.2 Collector Current vs. Case Temperature

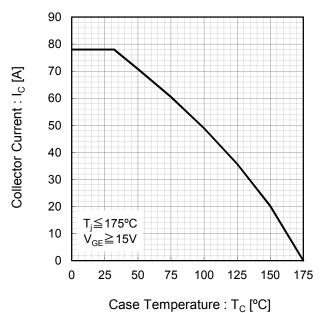


Fig.3 Forward Bias Safe Operating Area

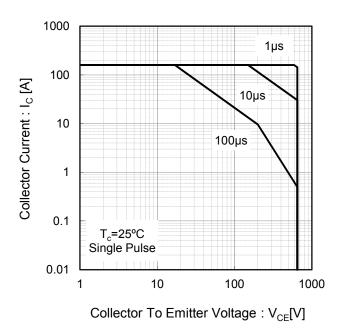
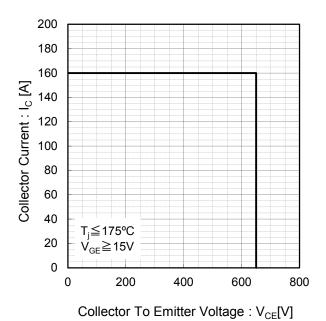


Fig.4 Reverse Bias Safe Operating Area



#### • Electrical Characteristic Curves

Fig.5 Typical Output Characteristics

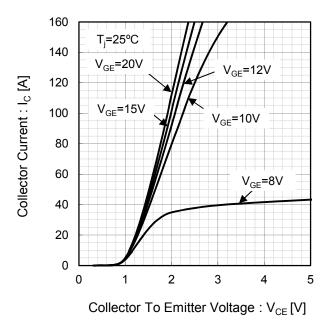
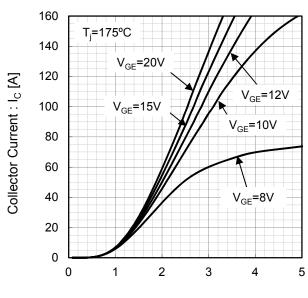


Fig.6 Typical Output Characteristics



Collector To Emitter Voltage :  $V_{CE}[V]$ 

Fig.7 Typical Transfer Characteristics

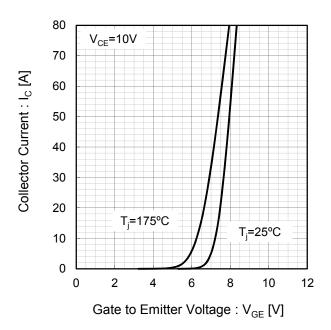
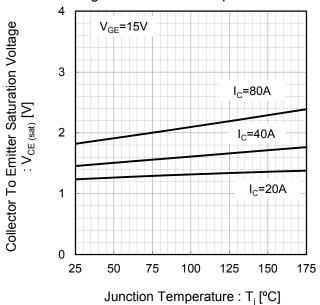
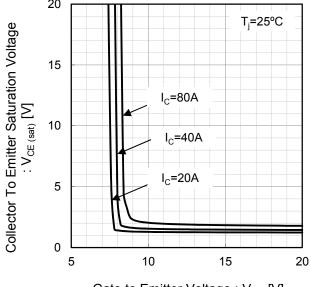


Fig.8 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature



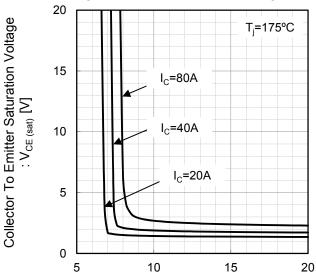
#### **•**Electrical Characteristic Curves

Fig.9 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage



Gate to Emitter Voltage :  $V_{GE}[V]$ 

Fig.10 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage



Gate to Emitter Voltage : V<sub>GE</sub> [V]

Fig.11 Typical Switching Time vs. Collector Current

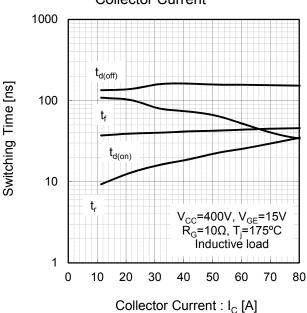
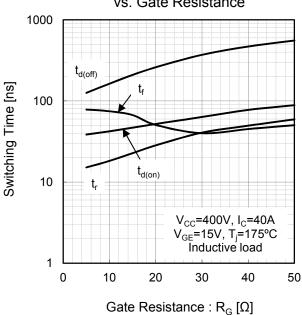


Fig.12 Typical Switching Time vs. Gate Resistance

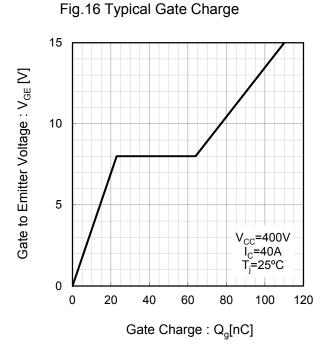


#### **•**Electrical Characteristic Curves

Fig.13 Typical Switching Energy Losses vs. Collector Current 10 Switching Energy Losses [mJ]  $\mathsf{E}_{\mathsf{off}}$ 1 0.1  $V_{CC}$ =400V,  $V_{GE}$ =15V R<sub>G</sub>=10 $\Omega$ , T<sub>j</sub>=175°C Inductive load 0.01 50 0 10 20 30 40 60 70 80 Collector Current : I<sub>C</sub> [A]

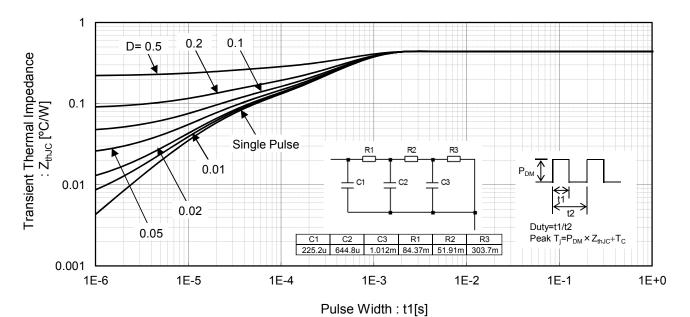
Fig.14 Typical Switching Energy Losses vs. Gate Resistance 10 Switching Energy Losses [mJ]  $\mathsf{E}_{\mathsf{off}}$ 1 E<sub>on</sub> 0.1 V<sub>CC</sub>=400V, I<sub>C</sub>=40A V<sub>GE</sub>=15V, T<sub>j</sub>=175°C Inductive load 0.01 10 30 40 0 20 50 Gate Resistance :  $R_G [\Omega]$ 

Fig.15 Typical Capacitance vs.
Collector To Emitter Voltage 10000 Cies 1000 Capacitance [pF] Coes 100 Cres 10 f=1MHz V<sub>GE</sub>=0V =25°C 0.01 0.1 1 10 100 Collector To Emitter Voltage :  $V_{CE}[V]$ 



#### • Electrical Characteristic Curves

Fig.17 Typical IGBT Transient Thermal Impedance



### •Inductive Load Switching Circuit and Waveform

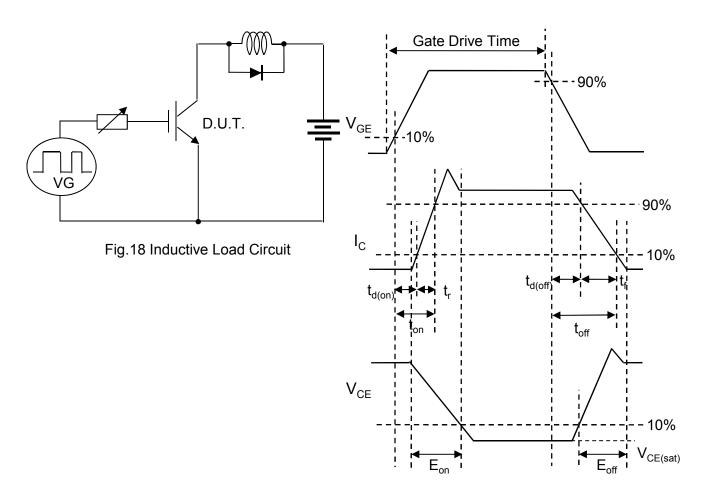


Fig.19 Inductive Load Waveform

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# RGW80TS65 - Web Page

Part Number	RGW80TS65
Package	TO-247N
Unit Quantity	450
Minimum Package Quantity	30
Packing Type	Tube
Constitution Materials List	inquiry
RoHS	Yes